
HVB14S

Silicon Epitaxial Planar PIN Diode for High Frequency
Attenuator

HITACHI

ADE-208-484(Z)
Rev 0

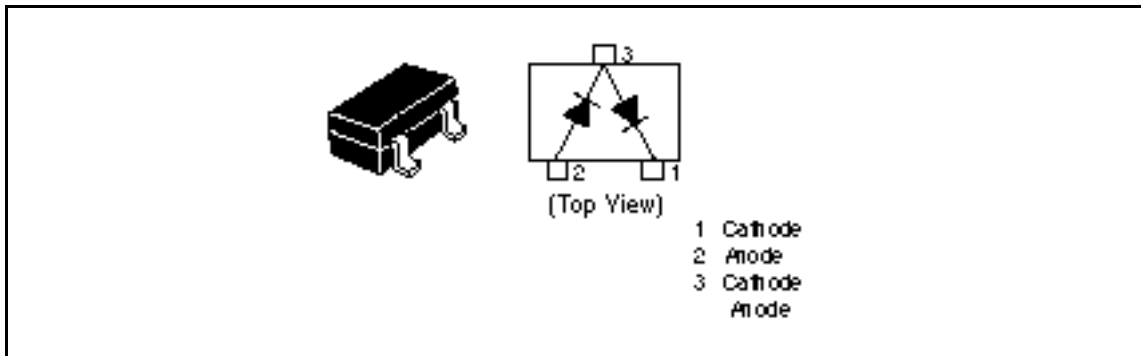
Features

- Σ Low forward resistance. ($r_f = 7.0\Omega_{\text{max}}$)
- Σ Low capacitance. ($C = 0.25\text{pF typ}$)
- Σ CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HVB14S	H6	CMPAK

Outline



HVB14S

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	50	V
Forward current	I_F	50	mA
Power dissipation	P_d ^{*1}	100	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

Note: 1. Two device total.

Electrical Characteristics (Ta = 25°C) ^{*2}

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	$I_F = 50$ mA
Reverse current	I_R	—	—	100	nA	$V_R = 50$ V
Capacitance	C	—	0.25	—	pF	$V_R = 50$ V, $f = 1$ MHz
Forward resistance	r_f	—	—	7	W	$I_F = 10$ mA, $f = 100$ MHz
ESD-Capability ^{*1}	—	200	—	—	V	C = 200pF, Both forward and reverse direction 1 pulse

Notes: 1. Failure criterion ; $I_R \geq 200$ nA at $V_R = 50$ V

2. Per one device.

Main Characteristic

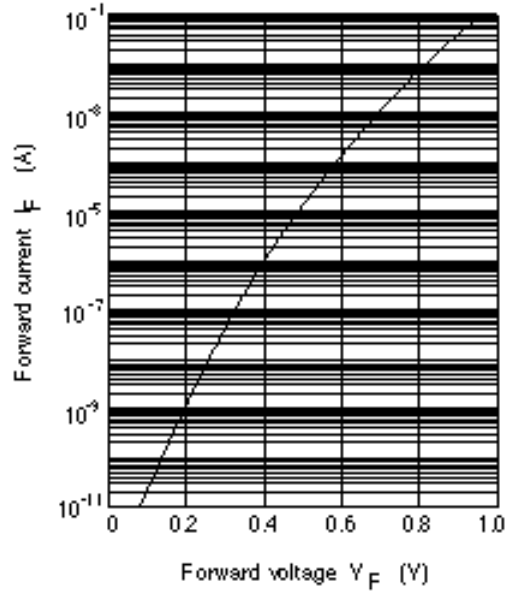


Fig.1 Forward current Vs. Forward voltage

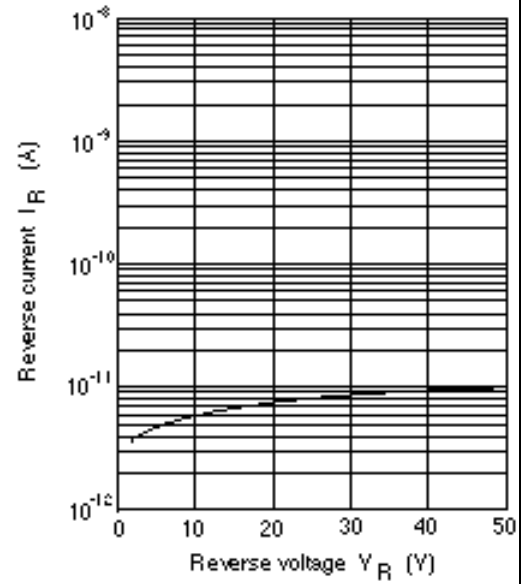


Fig.2 Reverse current Vs. Reverse voltage

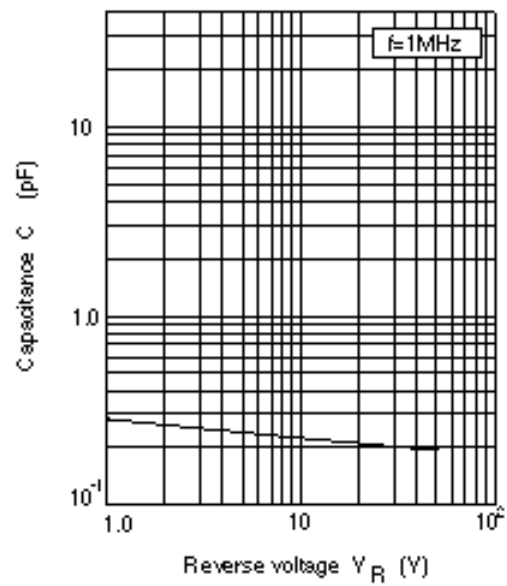


Fig.3 Capacitance Vs. Reverse voltage

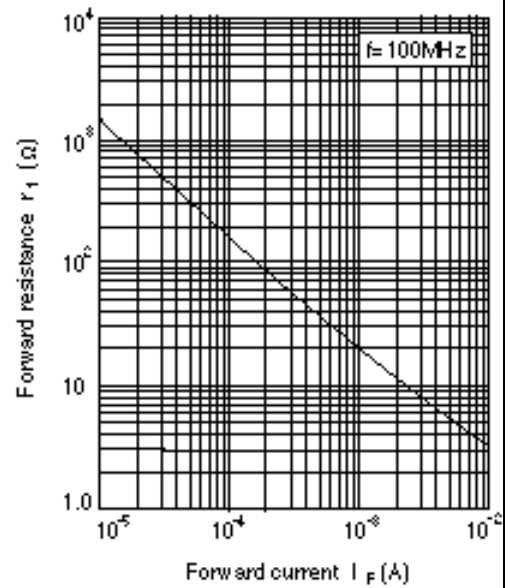


Fig.4 Forward resistance Vs. Forward current

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Package Dimensions

Unit : mm

